**April 2020** 





#### N-CHANNEL ENHANCEMENT MODE MOSFET

## **Product Summary**

BV <sub>DSS</sub>	R <sub>DS(ON)</sub> Max	I <sub>D</sub> Max T <sub>A</sub> = +25°C
201/	60mΩ @ V <sub>GS</sub> = 10V	2.7A
30V	100mΩ @ V <sub>GS</sub> = 4.5V	2.1A

## **Description and Applications**

This MOSFET is designed to minimize the on-state resistance (RDS(ON)) yet maintain superior switching performance, making it ideal for high-efficiency power management applications.

- General Purpose Interfacing Switch
- **Power Management Functions**
- **DC-DC Converters**
- Analog Switch

## **Features and Benefits**

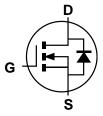
- Low On-Resistance
- Low Input Capacitance
- Fast Switching Speed
- Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)
- For automotive applications requiring specific change control (i.e. parts qualified to AEC-Q100/101/200, PPAP capable, and manufactured in IATF 16949 certified facilities), please contact us or your local Diodes representative. https://www.diodes.com/quality/product-definitions/

### Mechanical Data

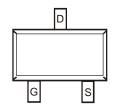
- Case: SOT323
- Case Material: Molded Plastic, "Green" Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminal Connections Indicator: See Diagram
- Terminals: Finish—Matte Tin Annealed over Copper Leadframe. Solderable per MIL-STD-202, Method 208 @3
- Weight: 0.027 grams (Approximate)







**Equivalent Circuit** 



Top View

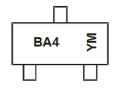
## Ordering Information (Note 4)

Part Number	Case	Packaging
DMN3061SW-7	SOT323	3,000/Tape & Reel
DMN3061SW-13	SOT323	10,000/Tape & Reel

Notes:

- 1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS), 2011/65/EU (RoHS 2) & 2015/863/EU (RoHS 3) compliant.
- 2. See https://www.diodes.com/quality/lead-free/ for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and
- 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
- 4. For packaging details, go to our website at https://www.diodes.com/design/support/packaging/diodes-packaging/

# **Marking Information**



BA4 = Product Type Marking Code YM or YM= Date Code Marking Y or  $\overline{Y}$ = Year (ex: H = 2020) M = Month (ex: 9 = September)

### Date Code Key

Year	2019	2020	2021	2022	2023	2024	2025	2026	2027	2028	2029	2030
Code	G	Н	- 1	J	K	L	М	N	0	Р	R	S
	1											
Month	Jan	Feb	Mar	Apr	May	Jun	Jul	Aug	Sep	Oct	Nov	Dec



# **Maximum Ratings** (@ $T_A = +25$ °C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit	
Drain-Source Voltage	VDSS	30	V	
Gate-Source Voltage		V <sub>GSS</sub>	±20	V
Continuous Drain Current (Note 6) V <sub>GS</sub> = 10V	ID	2.7 2.2	А	
Pulsed Drain Current (10µs Pulse, Duty Cycle = 1%	I <sub>DM</sub>	22	Α	
Maximum Body Diode Forward Current (Note 5)		Is	0.67	Α

# Thermal Characteristics ( $@T_A = +25^{\circ}C$ , unless otherwise specified.)

Characteristic		Symbol	Value	Unit
Total Power Dissipation (Note 5)		PD	0.49	W
Thermal Resistance, Junction to Ambient (Note 5)	Steady State	Rөja	254	°C/W
Total Power Dissipation (Note 6)		PD	0.65	W
Thermal Resistance, Junction to Ambient (Note 6)	Steady State	Reja	191	°C/W
Operating and Storage Temperature Range		T <sub>J,</sub> T <sub>STG</sub>	-55 to +150	°C

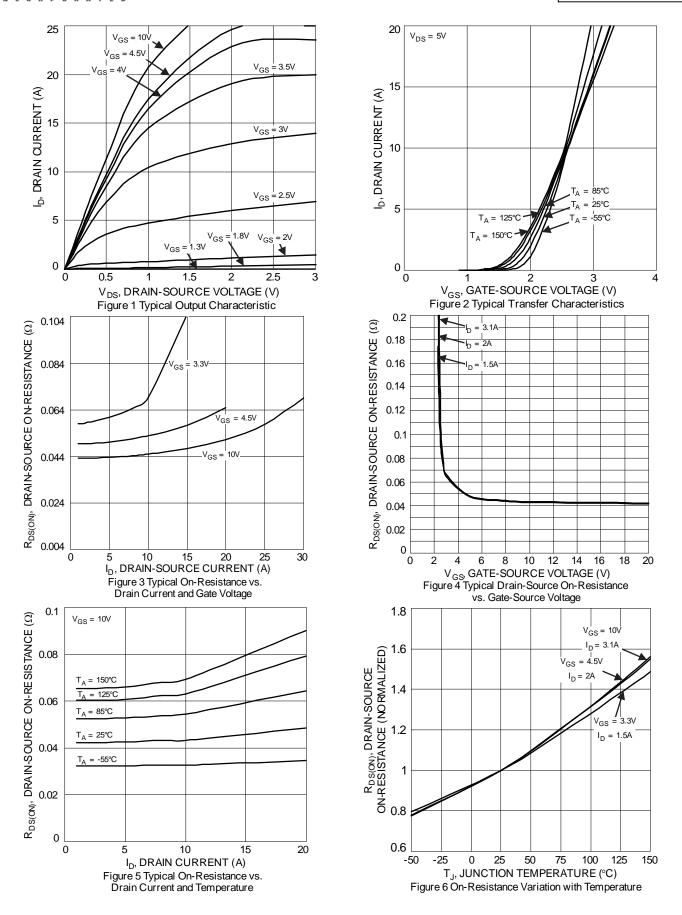
## Electrical Characteristics (@TA = +25°C, unless otherwise specified.)

Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition
OFF CHARACTERISTICS (Note 7)						
Drain-Source Breakdown Voltage	BV <sub>DSS</sub>	30	_	_	V	$V_{GS} = 0V, I_D = 250\mu A$
Zero Gate Voltage Drain Current @Tc = +25°C	IDSS	_	_	1.0	μA	V <sub>DS</sub> = 24V, V <sub>GS</sub> = 0V
Gate-Source Leakage	I <sub>GSS</sub>			±100	nA	$V_{GS} = \pm 20V$ , $V_{DS} = 0V$
ON CHARACTERISTICS (Note 7)						
Gate Threshold Voltage	V <sub>GS(TH)</sub>	0.5	_	1.8	V	$V_{DS} = V_{GS}$ , $I_D = 250\mu A$
		_	41	60		V <sub>GS</sub> = 10V, I <sub>D</sub> = 3.1A
Static Drain-Source On-Resistance	RDS(ON)		48	100	mΩ	V <sub>G</sub> S = 4.5V, I <sub>D</sub> = 2A
		_	56	200		$V_{GS} = 3.3V, I_D = 1.5A$
Diode Forward Voltage	VsD	_	0.7	1	V	Vgs = 0V, Is = 1A
DYNAMIC CHARACTERISTICS (Note 8)						
Input Capacitance	Ciss	_	278	_	pF	151/11/ 01/
Output Capacitance	Coss	_	44	_	pF	V <sub>DS</sub> = 15V, V <sub>GS</sub> = 0V, - f = 1.0MHz
Reverse Transfer Capacitance	Crss	_	29	_	pF	1 = 1.000112
Gate Resistance	Rg	_	4.2	_	Ω	$V_{DS} = 0V$ , $V_{GS} = 0V$ , $f = 1MHz$
Total Gate Charge	Qg	_	3.5	_	nC	
Gate-Source Charge	Qgs	_	0.1	_	nC	V <sub>DS</sub> = 15V, V <sub>GS</sub> = 4.5V, I <sub>D</sub> = 3A
Gate-Drain Charge	Qgd	_	1.3	_	nC	
Turn-On Delay Time	tD(ON)	_	5.7	_	ns	
Turn-On Rise Time	t <sub>R</sub>	_	97	_	ns	V <sub>GS</sub> = 10V, V <sub>DS</sub> = 15V,
Turn-Off Delay Time	tD(OFF)	_	12.6	_	ns	$R_G = 3\Omega$ , $R_L = 1.7\Omega$
Turn-Off Fall Time	t <sub>F</sub>	_	51	_	ns	

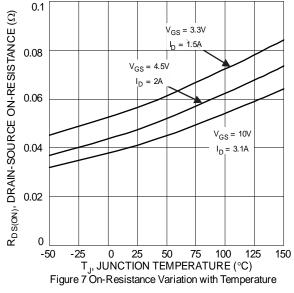
Notes:

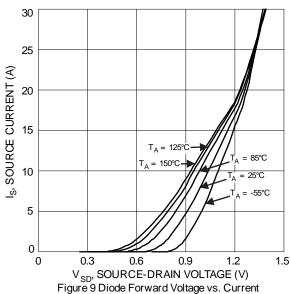
- Device mounted on FR-4 substrate PC board, with minimum recommended pad layout.
   Device mounted on FR-4 substrate PC board, 2oz copper, with thermal bias to bottom layer 1inch square copper plate.
   Short duration pulse test used to minimize self-heating effect.
   Guaranteed by design. Not subject to product testing.

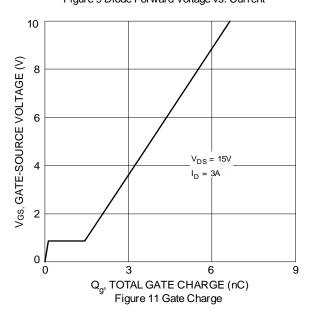












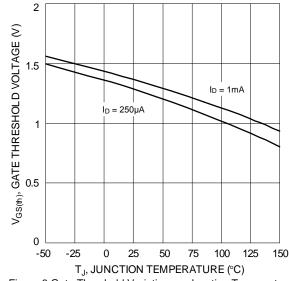
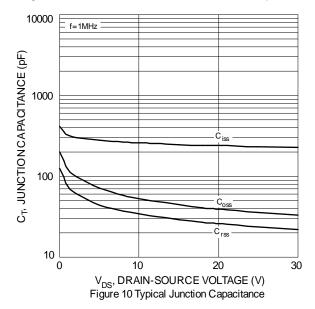


Figure 8 Gate Threshold Variation vs. Junction Temperature



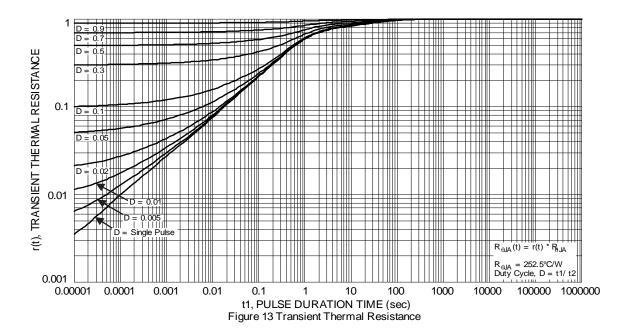
100

RDS(on)
Limited

PW = 1ms

PW = 100µs



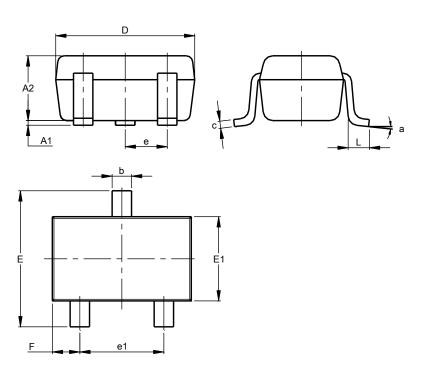




## **Package Outline Dimensions**

Please see http://www.diodes.com/package-outlines.html for the latest version.

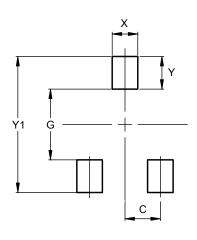
### **SOT323**



SOT323							
Dim	Min	Max	Тур				
A1	0.00	0.10	0.05				
A2	0.90	1.00	0.95				
b	0.25	0.40	0.30				
С	0.10	0.18	0.11				
D	1.80	2.20	2.15				
Ε	2.00	2.20	2.10				
E1	1.15	1.35	1.30				
е	C	0.650 BSC					
e1	1.20	1.40	1.30				
F	0.375	0.475	0.425				
L	0.25	0.40	0.30				
а	0°	8°					
All Dimensions in mm							

# **Suggested Pad Layout**

Please see http://www.diodes.com/package-outlines.html for the latest version.



### **SOT323**

Dimensions	Value (in mm)
С	0.650
G	1.300
X	0.470
Y	0.600
Y1	2.500



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